



Micro Commercial Components
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BUF405AXI

Features

- High voltage, high speed switching NPN transistors.
- With TO-220F package
- Intended for use in horizontal deflection circuits of color television receivers

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	450	V
V_{CBO}	Collector-Base Voltage	1000	V
V_{EBO}	Emitter-Base Voltage	9.0	V
I_{CP}	Peak Collector Current	10	A
I_C	Collector Current	7.5	A
P_C	Collector power dissipation	80	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

NPN Silicon Power Transistors

Electrical Characteristics @ 25°C Unless Otherwise Specified

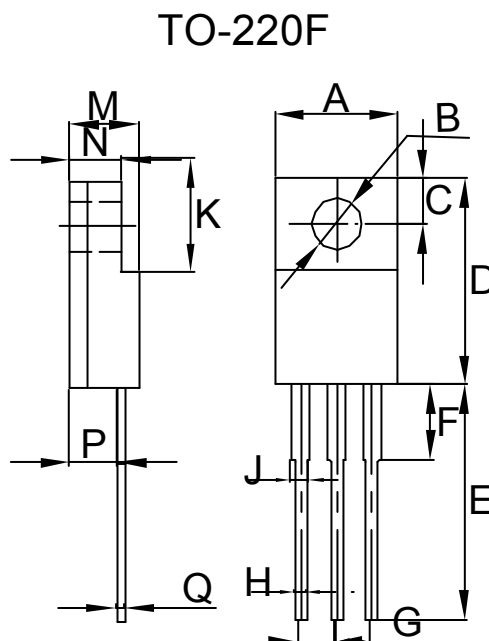
Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=100\text{mA}$, $I_E=0$)	450	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=1000\text{Vdc}$, $I_E=0$)	---	1.0	mA
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=9.0\text{Vdc}$, $I_C=0$)	---	10	mA

ON CHARACTERISTICS

h_{FE-1}	Forward Current Transfer ratio ($I_C=5.0\text{mA}$, $V_{CE}=5.0\text{Vdc}$)	10	35	---
h_{FE-2}	Forward Current Transfer ratio ($I_C=500\text{mA}$, $V_{CE}=5.0\text{Vdc}$)	10	35	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=2.5\text{A}$, $I_E=0.5\text{A}$)	---	1.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=2.5\text{A}$, $I_E=0.5\text{A}$)	---	1.3	Vdc



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.388	.407	9.85	10.35	
B	.128	.145	3.25	3.65	
C	.101	.111	2.57	2.83	
D	.670	.810	14.9	18.5	
E	.496	.520	12.6	13.2	
F	.148	.167	3.75	4.25	
G	.096	.101	2.44	2.57	
H	.019	.029	.47	.73	
J	.046	.056	1.17	1.43	
K	.266	.285	6.75	7.25	
M	.165	.190	4.25	4.75	
N	.110	.130	2.81	3.31	
P	.097	.107	2.72	2.48	
Q	.019	.029	.47	.73	